Silicon PNP Power Transistors 2SA648

DESCRIPTION

·With TO-3 package
·Wide area of safe operation

APPLICATIONS

·For low frequency and large power switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-7	A
I_{CM}	Collector current-peak		-11	A
P_C	Collector power dissipation	T_C=25□	60	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-25mA ;I_B=0	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ;I_E=0	-120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ;I_C=0	-6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A; I_B=-0.5A			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-5A; I_B=-0.5A			-2.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-0.1	mA
h_{FE}	DC current gain	I_C=-3A ; V_{CE}=-5V	30		120	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		10		MHz

PACKAGE OUTLINE

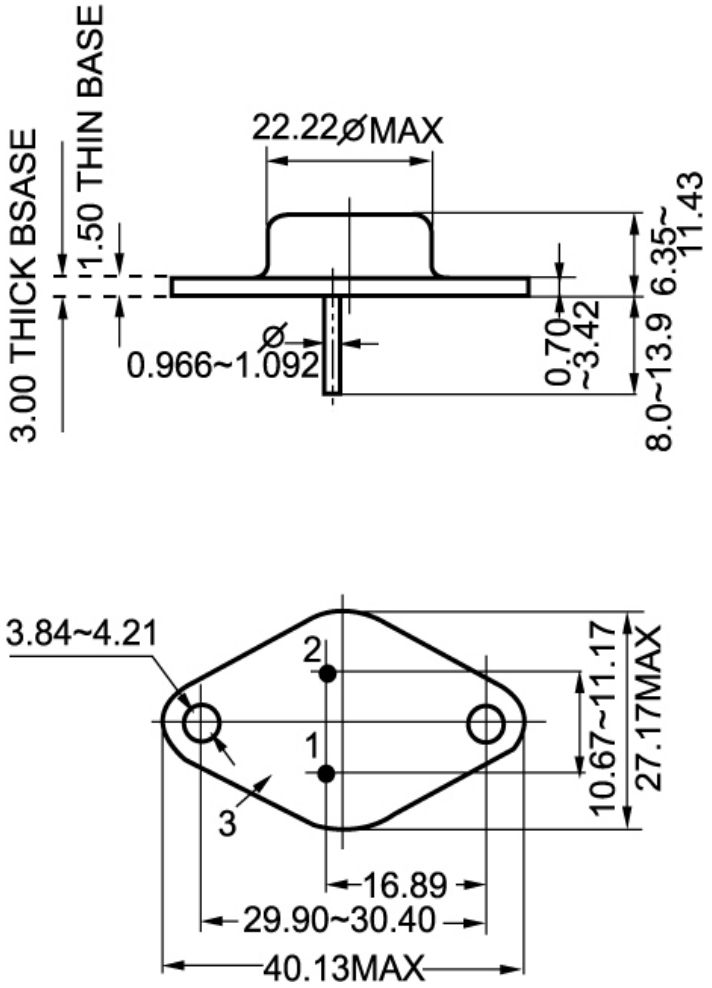


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)